

74HC423; 74HCT423

Dual retriggerable monostable multivibrator with reset

Rev. 03 — 24 July 2008

Product data sheet

1. General description

74HC423; 74HCT423 are high-speed Si-gate CMOS devices that are pin compatible with low power Schottky TTL (LSTTL). They are specified in compliance with JEDEC standard no. 7A.

The 74HC423; 74HCT423 dual retriggerable monostable multivibrator with reset has two methods of output pulse width control.

1. The minimum pulse width is essentially determined by the selection of an external resistor (R_{EXT}) and capacitor (C_{EXT}), see [Section 12.1](#).
2. Once triggered, the basic output pulse width may be extended by retriggering the gated active LOW-going edge input ($n\bar{A}$) or the active HIGH-going edge input (nB). By repeating this process, the output pulse period ($nQ = \text{HIGH}$, $n\bar{Q} = \text{LOW}$) can be made as long as desired. When $n\bar{RD}$ is LOW, it forces the nQ output LOW, the $n\bar{Q}$ output HIGH and also inhibits the triggering. [Figure 10](#) and [Figure 11](#) illustrate pulse control by reset.

The $n\bar{A}$ and nB inputs' Schmitt trigger action makes them highly tolerant to slower input rise and fall times.

The 74HC423; 74HCT423 are identical to the 74HC123; 74HCT123 except that they cannot be triggered via the reset input.

2. Features

- DC triggered from active HIGH or active LOW inputs
- Retriggerable for very long pulses up to 100% duty factor
- Direct reset terminates output pulse
- Schmitt-trigger action on all inputs except for the reset input
- Complies with JEDEC standard no. 7A
- ESD protection:
 - ◆ HBM JESD22-A114E exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
- Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC423N	−40 °C to +125 °C	DIP16	plastic dual in-line package; 16 leads (300 mil)	SOT38-4
74HCT423N				
74HC423D	−40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74HCT423D				
74HC423BQ	−40 °C to +125 °C	DHVQFN16	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 × 3.5 × 0.85 mm	SOT763-1
74HCT423BQ				
74HCT423DB	−40 °C to +125 °C	SSOP16	plastic shrink small outline package; 16 leads; body width 5.3 mm	SOT338-1
74HCT423PW	−40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1

4. Functional diagram

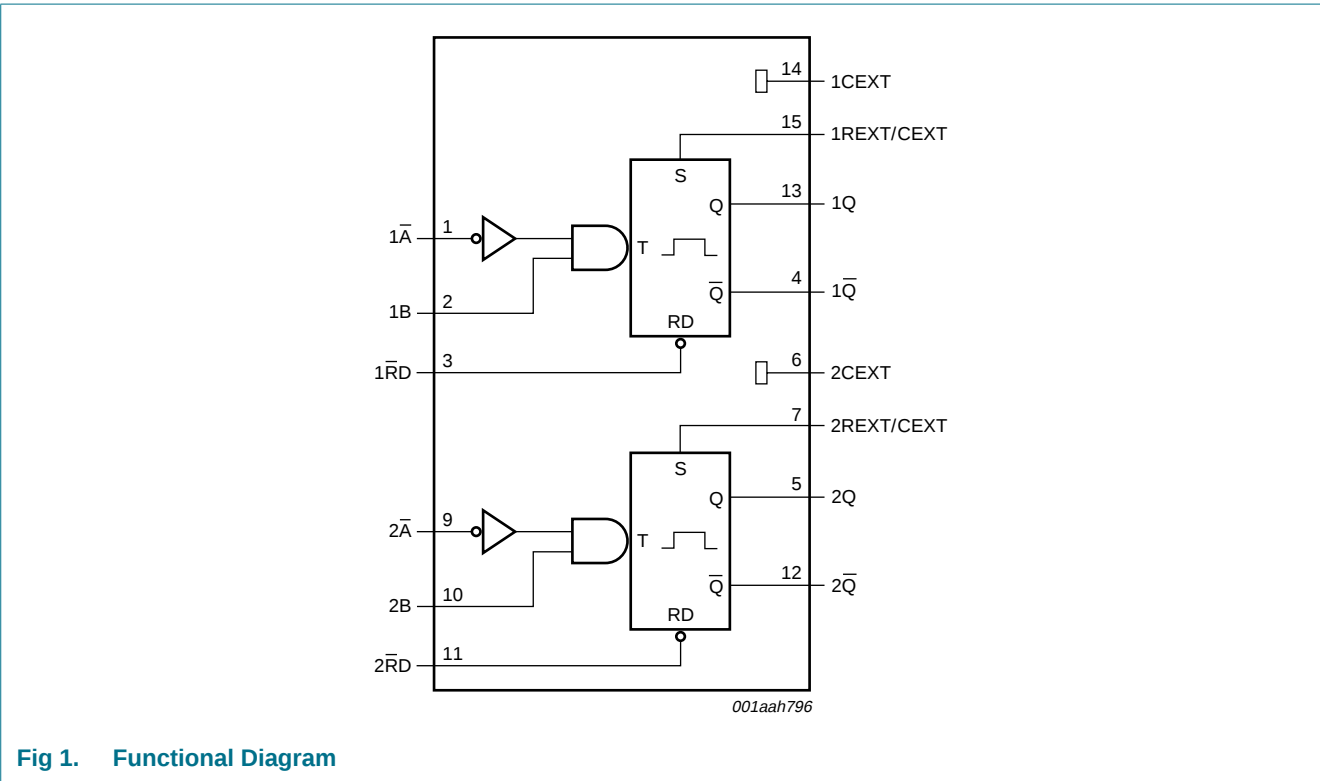


Fig 1. Functional Diagram

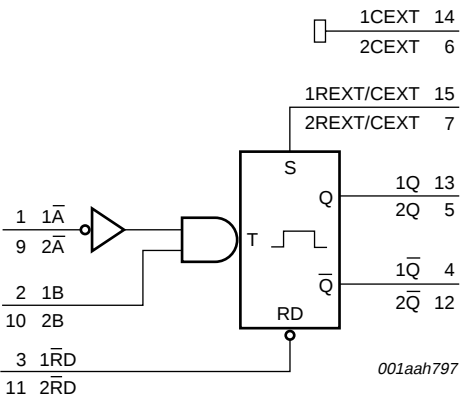


Fig 2. Logic symbol

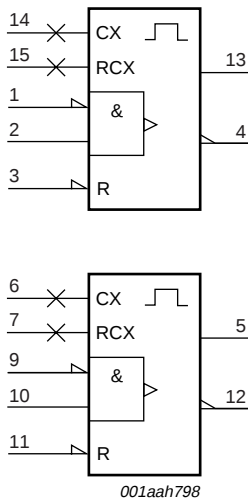


Fig 3. IEC Logic symbol

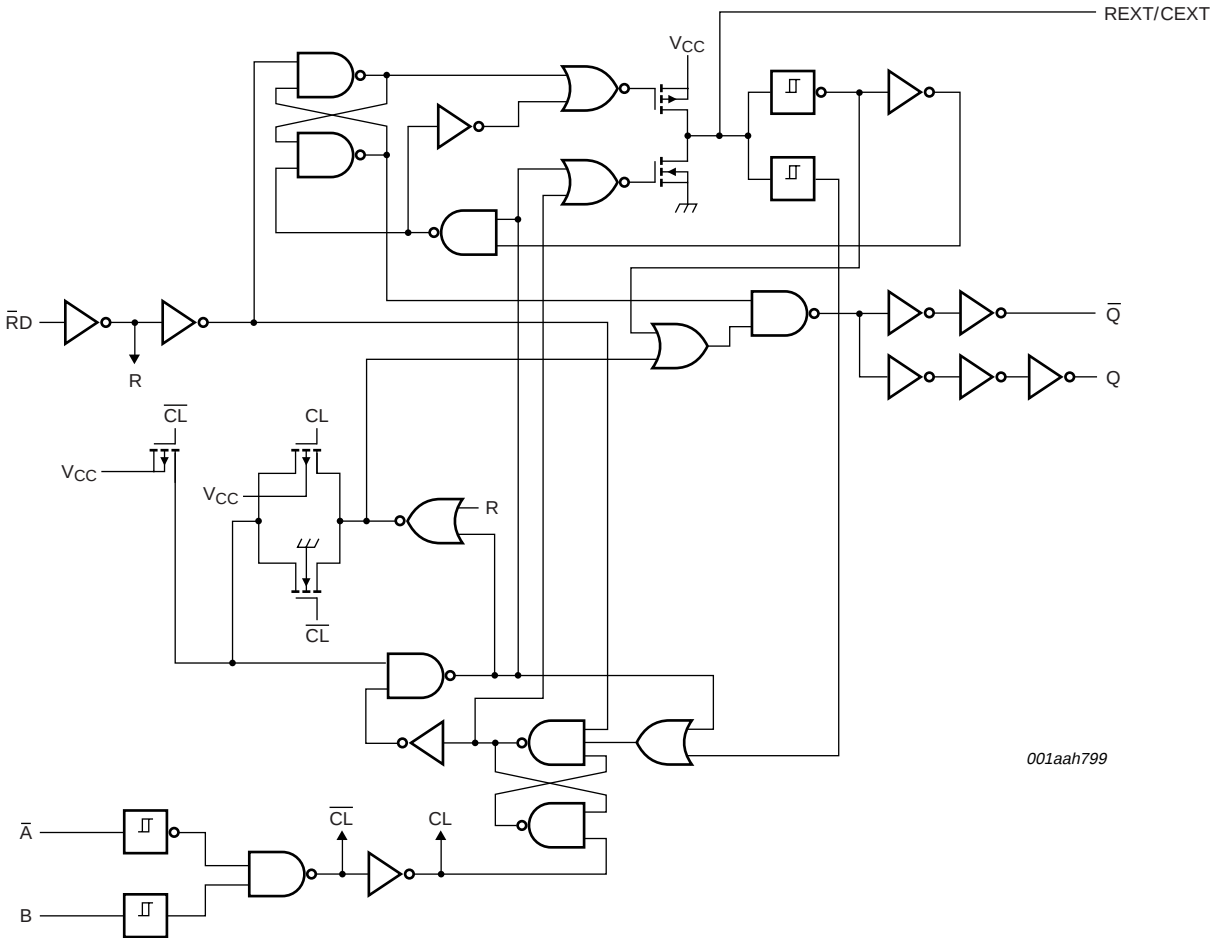


Fig 4. Logic diagram

5. Pinning information

5.1 Pinning

74HC423
74HCT423

1A 1 16 VCC
1B 2 15 1REXT/CEXT
1RD 3 14 1CEXT
1Q 4 13 1Q
2Q 5 12 2Q
2CEXT 6 11 2RD
2REXT/CEXT 7 10 2B
GND 8 9 2A

001aah785

74HC423
74HCT423

terminal 1 index area
1A 1 16 VCC
1B 2 15 1REXT/CEXT
1RD 3 14 1CEXT
1Q 4 13 1Q
2Q 5 12 2Q
2CEXT 6 11 2RD
2REXT/CEXT 7 10 2B
GND 8 9 2A

001aah784

Transparent top view

(1) The die substrate is attached to this pad using a conductive die attach material. It cannot be used as supply pin or input

Fig 5. Pin configuration DIP16, SO16 and (T)SSOP16

Fig 6. Pin configuration DHVQFN16

5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1A, 2A	1, 9	trigger input (negative edge triggered)
1B, 2B	2, 10	trigger input (positive edge triggered)
1RD, 2RD	3, 11	direct reset (active LOW)
1Q, 2Q	4, 12	output (active LOW)
GND	8	ground (0 V)
1Q, 2Q	13, 5	output (active HIGH)
1CEXT, 2CEXT	14, 6	external capacitor connection
1REXT/CEXT, 2REXT/CEXT	15, 7	external resistor/capacitor connection
VCC	16	supply voltage

6. Functional description

Table 3. Function table^[1]

Input			Output	
nRD	nA	nB	nQ	nQ
L	X	X	L	H
X	H	X	L ^[2]	H ^[2]
X	X	L	L ^[2]	H ^[2]
H	L	↑		
H	↓	H		

[1] H = HIGH voltage level;

L = LOW voltage level;

X = don't care;

↑ = LOW-to-HIGH transition;

↓ = HIGH-to-LOW transition;

 = one HIGH level output pulse;

 = one LOW level output pulse.

[2] If the monostable multivibrator was triggered before this condition was established, the pulse will continue as programmed.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7	V
I _{IK}	input clamping current	V _I < -0.5 V or V _I > V _{CC} + 0.5 V	^[1] -	±20	mA
I _{OK}	output clamping current	V _O < -0.5 V or V _O > V _{CC} + 0.5 V	^[1] -	±20	mA
I _O	output current	-0.5 V < V _O < V _{CC} + 0.5 V	-	±25	mA
I _{CC}	supply current		-	50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	DIP16 package	^[2] -	750	mW
		SO16, SSOP16, TSSOP16 and DHVQFN16 packages	^[3] -	500	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For DIP16 packages: above 70 °C the value of P_{tot} derates linearly at 12 mW/K.

[3] For SO16 packages: above 70 °C the value of P_{tot} derates linearly at 8 mW/K;

For SSOP16 and TSSOP16 packages: above 60 °C the value of P_{tot} derates linearly at 5.5 mW/K;

For DHVQFN16 packages: above 60 °C the value of P_{tot} derates linearly at 4.5 mW/K.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74HC423			74HCT423			Unit
			Min	Typ	Max	Min	Typ	Max	
V _{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V _I	input voltage		0	-	V _{CC}	0	-	V _{CC}	V
V _O	output voltage		0	-	V _{CC}	0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	-	+125	-40	-	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V _{CC} = 2.0 V	-	-	625	-	-	-	ns/V
		V _{CC} = 4.5 V	-	1.67	139	-	1.67	139	ns/V
		V _{CC} = 6.0 V	-	-	83	-	-	-	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HC423										
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
		V _{CC} = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		V _{CC} = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
		V _{CC} = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		V _{CC} = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = −20 μA; V _{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I _O = −20 μA; V _{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = −20 μA; V _{CC} = 6.0 V	5.9	6.0	-	5.9	-	5.9	-	V
		I _O = −4.0 mA; V _{CC} = 4.5 V	3.98	4.32	-	3.84	-	3.7	-	V
		I _O = −5.2 mA; V _{CC} = 6.0 V	5.48	5.81	-	5.34	-	5.2	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = 20 μA; V _{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 20 μA; V _{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 20 μA; V _{CC} = 6.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 4.0 mA; V _{CC} = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
		I _O = 5.2 mA; V _{CC} = 6.0 V	-	0.16	0.26	-	0.33	-	0.4	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 6.0 V	-	-	±0.1	-	±1.0	-	±1.0	μA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 6.0 V	-	-	8.0	-	80	-	160	μA

Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
C _I	input capacitance		-	3.5	-	-	-	-	-	pF
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V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V								
		I _O = –20 µA	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = –4.0 mA	3.98	4.32	-	3.84	-	3.7	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V								
		I _O = 20 µA	-	0	0.1	-	0.1	-	0.1	V
		I _O = 4.0 mA	-	0.15	0.26	-	0.33	-	0.4	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	±0.1	-	±1.0	-	±1.0	µA
I _{CC}	supply current	V _I = V _{CC} or GND; V _{CC} = 5.5 V; I _O = 0 A	-	-	8.0	-	80	-	160	µA
ΔI _{CC}	additional supply current	per input pin; V _I = V _{CC} – 2.1 V; other inputs at V _{CC} or GND; V _{CC} = 4.5 V to 5.5 V; I _O = 0 A								
		n $\bar{A}$, nB inputs	-	35	126	-	158	-	172	µA
		nRD input	-	50	180	-	225	-	245	µA
C _I	input capacitance		-	3.5	-	-	-	-	-	pF

10. Dynamic characteristics

Table 7. Dynamic characteristics

$GND = 0\text{ V}$; test circuit see [Figure 12](#).

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HC423										
t _{pd}	propagation delay	n $\overline{A}$ or nB to nQ or n $\overline{Q}$; R _{EXT} = 5 k Ω ; C _{EXT} = 0 pF; see Figure 7 [1]								
		V _{CC} = 2.0 V	-	80	255	-	320	-	385	ns
		V _{CC} = 4.5 V	-	29	51	-	64	-	77	ns
		V _{CC} = 5.0 V; C _L = 15 pF	-	25	-	-	-	-	-	ns
		V _{CC} = 6.0 V	-	23	43	-	54	-	65	ns
		n $\overline{RD}$ to nQ or n $\overline{Q}$; see Figure 7 [1]								
		V _{CC} = 2.0 V	-	66	215	-	270	-	325	ns
		V _{CC} = 4.5 V	-	24	43	-	54	-	65	ns
		V _{CC} = 5.0 V; C _L = 15 pF	-	20	-	-	-	-	-	ns
		V _{CC} = 6.0 V	-	19	37	-	46	-	55	ns
t _t	transition time	see Figure 7 [2]								
		V _{CC} = 2.0 V	-	19	75	-	95	-	110	ns
		V _{CC} = 4.5 V	-	7	15	-	19	-	22	ns
		V _{CC} = 6.0 V	-	6	13	-	16	-	19	ns
t _w	pulse width	n $\overline{A}$ input LOW; see Figure 7 and Figure 8								
		V _{CC} = 2.0 V	100	11	-	125	-	150	-	ns
		V _{CC} = 4.5 V	20	4	-	25	-	30	-	ns
		V _{CC} = 6.0 V	17	3	-	21	-	26	-	ns
		nB input HIGH; see Figure 7 and Figure 8								
		V _{CC} = 2.0 V	100	17	-	125	-	150	-	ns
		V _{CC} = 4.5 V	20	6	-	25	-	30	-	ns
		V _{CC} = 6.0 V	17	5	-	21	-	26	-	ns
		n $\overline{RD}$ input LOW; see Figure 7 and Figure 8								
		V _{CC} = 2.0 V	100	14	-	125	-	150	-	ns
		V _{CC} = 4.5 V	20	5	-	25	-	30	-	ns
		V _{CC} = 6.0 V	17	4	-	21	-	26	-	ns
		nQ HIGH or n $\overline{Q}$ LOW; V _{CC} = 5.0 V; R _{EXT} = 10 k Ω ; C _{EXT} = 100 nF; see Figure 7 and Figure 8	-	450	-	-	-	-	-	μ s
		nQ HIGH or n $\overline{Q}$ LOW; V _{CC} = 5.0 V; R _{EXT} = 5 k Ω ; C _{EXT} = 0 pF; V _I = GND to V _{CC} ; see Figure 7 and Figure 8 [3]	-	75	-	-	-	-	-	ns
t _{rtrig}	retrigger time	n $\overline{A}$ or nB input; V _{CC} = 5.0 V; R _{EXT} = 5 k Ω ; C _{EXT} = 0 pF; see Figure 10 [4]	-	110	-	-	-	-	-	ns

Table 7. Dynamic characteristics ...continuedGND = 0 V; test circuit see [Figure 12](#).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
R _{EXT}	external timing resistor	V _{CC} = 2.0 V; see Figure 8	10	-	1000	-	-	-	-	kΩ
		V _{CC} = 5.0 V	2	-	1000	-	-	-	-	kΩ
C _{EXT}	external timing capacitor	V _{CC} = 5.0 V; see Figure 8 [5]	no limits							pF
C _{PD}	power dissipation capacitance	per package; V _I = GND to V _{CC} [6]	-	54	-	-	-	-	-	pF

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t _{pd}	propagation delay	n $\overline{A}$ or nB to nQ or n $\overline{Q}$; R _{EXT} = 5 kΩ; C _{EXT} = 0 pF; see Figure 7								
		V _{CC} = 4.5 V [1]	-	30	51	-	64	-	77	ns
		V _{CC} = 5.0 V; C _L = 15 pF [1]	-	26	-	-	-	-	-	ns
		n $\overline{RD}$ to nQ or n $\overline{Q}$; R _{EXT} = 5 kΩ; C _{EXT} = 0 pF; see Figure 7 [1]	-	26	48	-	60	-	72	ns
		V _{CC} = 4.5 V [1]	-	26	48	-	60	-	72	ns
		V _{CC} = 5.0 V; C _L = 15 pF [1]	-	22	-	-	-	-	-	ns
t _t	transition time	V _{CC} = 4.5 V; Figure 7 [2]	-	7	15	-	19	-	22	ns
t _w	pulse width	trigger pulse; n $\overline{A}$ input LOW; V _{CC} = 4.5 V; see Figure 7 and Figure 10	20	5	-	25	-	30	-	ns
		trigger pulse; nB input HIGH; V _{CC} = 4.5 V; see Figure 7 and Figure 10	20	5	-	25	-	30	-	ns
		reset pulse; n $\overline{RD}$ input LOW; V _{CC} = 4.5 V; see Figure 7 and Figure 11	20	7	-	25	-	30	-	ns
		output pulse; nQ HIGH or n $\overline{Q}$ LOW; V _{CC} = 5.0 V; R _{EXT} = 10 kΩ; C _{EXT} = 100 nF; see Figure 7 , Figure 10 and Figure 11	-	450	-	-	-	-	-	μs
		output pulse; nQ HIGH or n $\overline{Q}$ LOW; V _{CC} = 5.0 V; R _{EXT} = 5 kΩ; C _{EXT} = 0 pF; V _I = GND to V _{CC} – 1.5 V; see Figure 7 , Figure 10 and Figure 11 [3]	-	75	-	-	-	-	-	ns
t _{trig}	retrigger time	n $\overline{A}$ or nB input; V _{CC} = 5.0 V; R _{EXT} = 5 kΩ; C _{EXT} = 0 pF; see Figure 10	-	110	-	-	-	-	-	ns
R _{EXT}	external timing resistor	V _{CC} = 5.0 V; see Figure 8	2	-	1000	-	-	-	-	kΩ
C _{EXT}	external timing capacitor	V _{CC} = 5.0 V; see Figure 8 [5]	no limits							pF

Table 7. Dynamic characteristics ...continuedGND = 0 V; test circuit see [Figure 12](#).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
C _{PD}	power dissipation capacitance	per package; V _I = GND to V _{CC} – 1.5 V [6]	-	56	-	-	-	-	-	pF

[1] t_{pd} is the same as t_{PHL} and t_{PLH}.[2] t_t is the same as t_{THL} and t_{TLH}.[3] For other R_{EXT} and C_{EXT} combinations see [Figure 8](#). If C_{EXT} > 10 pF, the next formula is valid:t_W = K × R_{EXT} × C_{EXT} (typ.), where:t_W = output pulse width in ns;R_{EXT} = external resistor in kΩ;C_{EXT} = external capacitor in pF;K = 0.55 for V_{CC} = 2.0 V and 0.45 for V_{CC} = 5.0 V; see [Figure 9](#).

Inherent test jig and pin capacitance at pins 15 and 7 (nREXT/CEXT) is 7 pF.

[4] The time to retrigger the monostable multivibrator depends on the values of R_{EXT} and C_{EXT}. The output pulse width will only be extended when the time between the active-going edges of the trigger input pulses meets the minimum retrigger time.If C_{EXT} > 10 pF, the next formula (at V_{CC} = 5.0 V) for the set-up time of a retrigger pulse is valid:t_{rtrig} = 30 + 0.19 × R_{EXT} × C_{EXT}^{0.9} + 13 × R_{EXT}^{1.05} (typ.); where:t_{rtrig} = retrigger time in ns;C_{EXT} = external capacitor in pF;R_{EXT} = external resistor in kΩ.

Inherent test jig and pin capacitance at pins 15 and 7 (nREXT/CEXT) is 7 pF.

[5] When the device is powered-up, initiate the device via a reset pulse, when C_{EXT} < 50 pF.[6] C_{PD} is used to determine the dynamic power dissipation (P_D in μW):P_D = C_{PD} × V_{CC}² × f_i × N + Σ (C_L × V_{CC}² × f_o); where:f_i = input frequency in MHz;f_o = output frequency in MHz;C_L = output load capacitance in pF;V_{CC} = supply voltage in V;

N = number of inputs switching;

Σ (C_L × V_{CC}² × f_o) = sum of outputs.

11. Waveforms

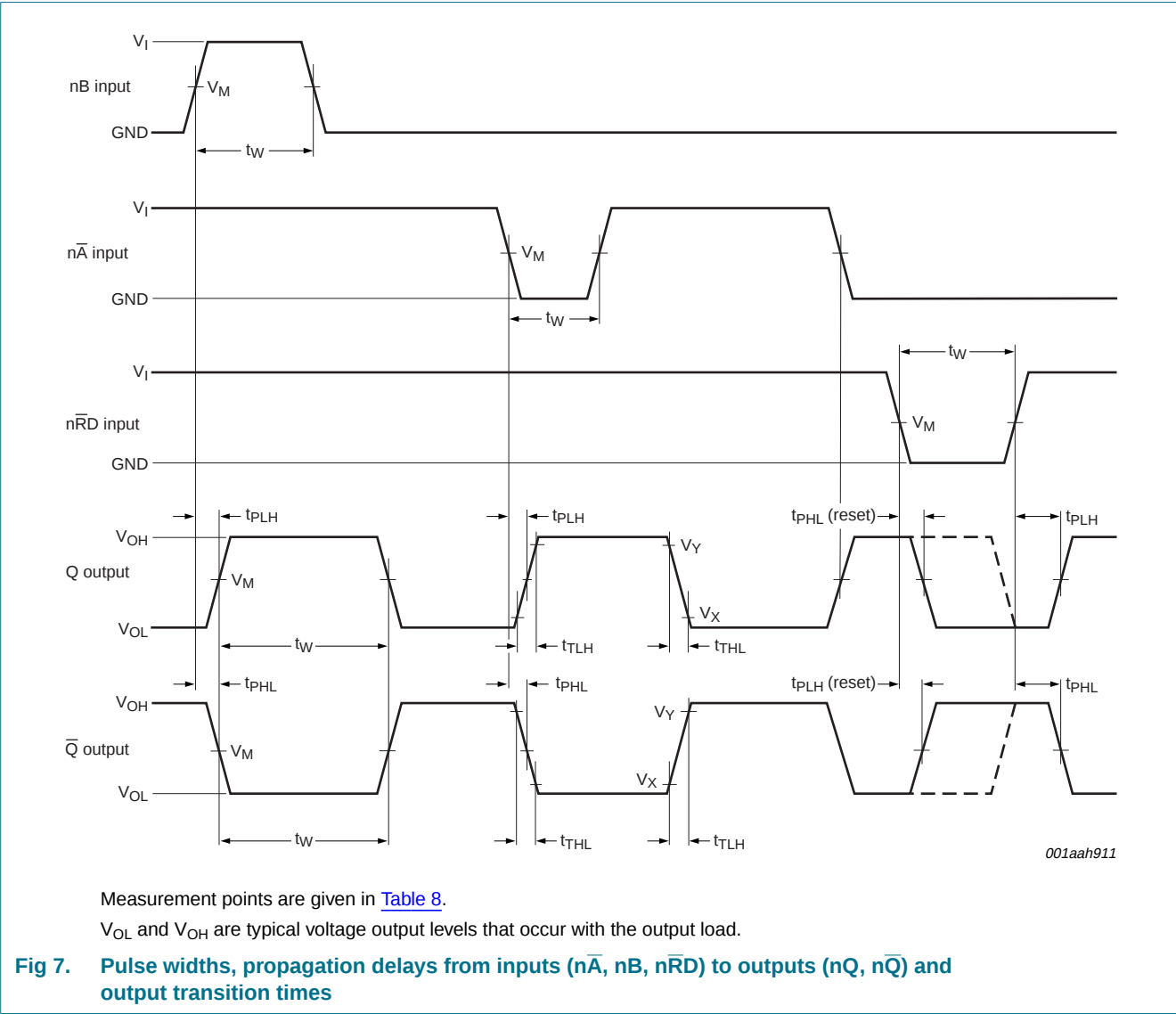
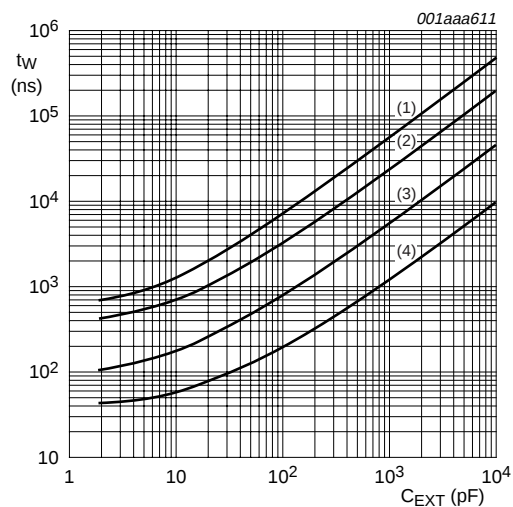


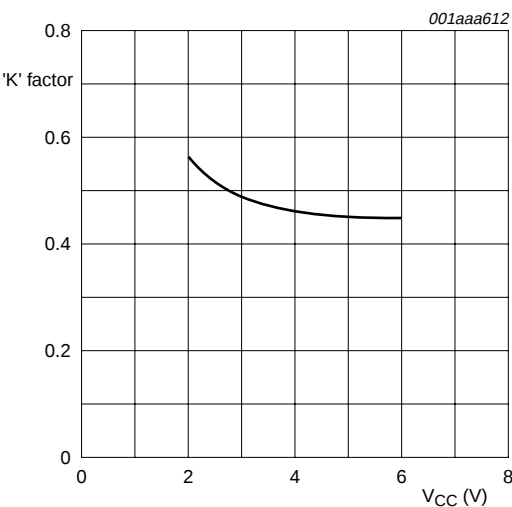
Table 8. Measurement points

Type	Input		Output		
	V_I	V_M	V_M	V_X	V_Y
74HC423	V_{CC}	$0.5V_{CC}$	$0.5V_{CC}$	$0.1V_{CC}$	$0.9V_{CC}$
74HCT423	3 V	1.3 V	1.3 V	$0.1V_{CC}$	$0.9V_{CC}$



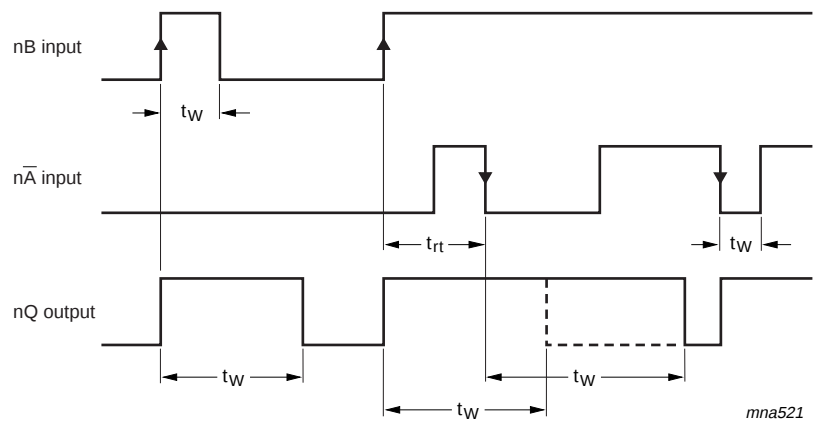
$V_{CC} = 5.0\text{ V}$ and $T_{amb} = 25\text{ }^{\circ}\text{C}$.
(1) $R_{EXT} = 100\text{ k}\Omega$.
(2) $R_{EXT} = 50\text{ k}\Omega$.
(3) $R_{EXT} = 10\text{ k}\Omega$.
(4) $R_{EXT} = 2\text{ k}\Omega$.

Fig 8. Typical output pulse width as a function of the external capacitor values



External capacitance = 10 nF,
external resistance = 10 kΩ to 100 kΩ and $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Fig 9. Typical 'K' factor



$n\overline{RD} = \text{HIGH}$.

Fig 10. Output pulse control using retrigger pulse (t_{trig})

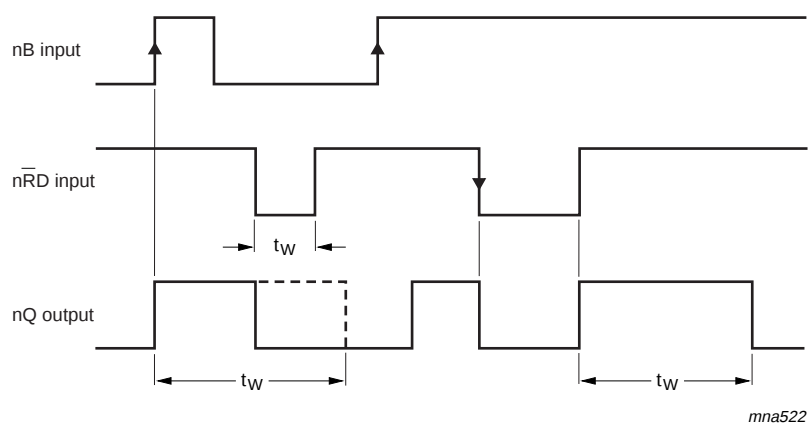
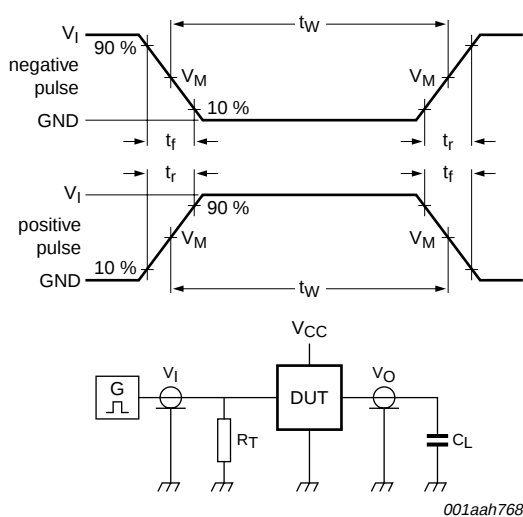

$$n\bar{A} = \text{LOW.}$$

Fig 11. Output pulse control using reset input nRD



Test data is given in [Table 9](#).

Definitions for test circuit:

R_T = Termination resistance should be equal to output impedance Z_0 of the pulse generator.

C_L = Load capacitance including jig and probe capacitance.

Fig 12. Test circuit for measuring switching times

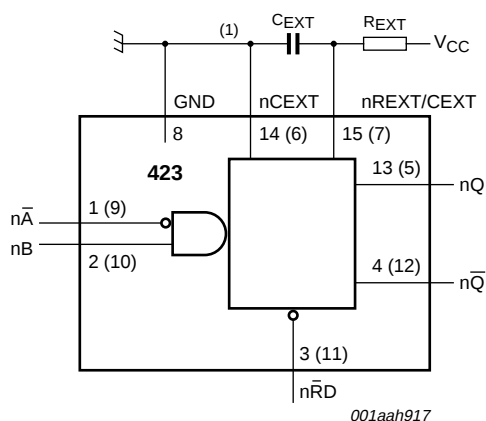
Table 9. Test data

Supply	Input		Load
V_{CC}	V_I	t_r, t_f	C_L
2.0 V to 6.0 V	V _{CC}	6 ns	15 pF, 50 pF

12. Application information

12.1 Timing component connections

The basic output pulse width is essentially determined by the values of the external timing components R_{EXT} and C_{EXT} .



- (1) For minimum noise generation it is recommended that the nCEXT pins (6, 14) are connected to ground externally to the GND pin (8).

Fig 13. Timing component connections

12.1.1 Minimum monostable pulse width

To set the minimum pulse width, when $C_{EXT} < 10$ nF, see [Figure 8](#) and when $C_{EXT} > 10$ nF, the output pulse width is defined as:

$t_W = 0.45 \times R_{EXT} \times C_{EXT}$ (typ.), where:

t_W = pulse width in μ s;

R_{EXT} = external resistor in k Ω ;

C_{EXT} = external capacitor in nF.

12.2 Power-up considerations

When the monostable is powered-up it may produce an output pulse, with a pulse width defined by the values of R_{EXT} and C_{EXT} , this output pulse can be eliminated using the circuit shown in [Figure 14](#).

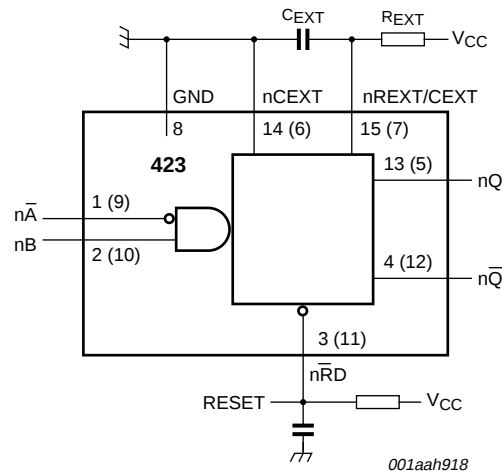


Fig 14. Power-up output pulse elimination circuit

12.3 Power-down considerations

A large capacitor C_{EXT} may cause problems when powering-down the monostable due to the capacitor's stored energy. When a system containing this device is powered-down or a rapid decrease of V_{CC} to zero occurs, the monostable may sustain damage, due to the capacitor discharging through the input protection diodes. To avoid this possibility, use a damping diode D_{EXT} preferably a germanium or Schottky type diode able to withstand large current surges and connect as shown in [Figure 15](#).

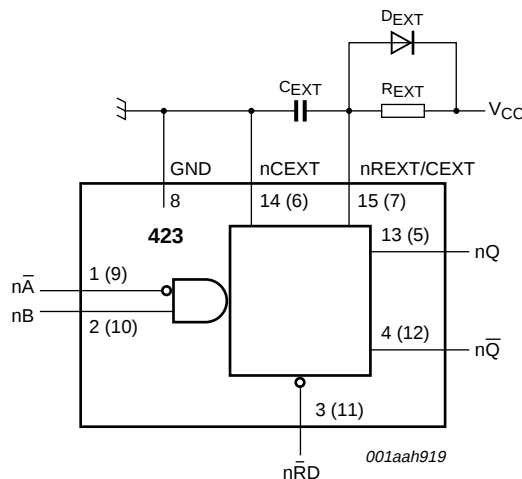


Fig 15. Power-down protection circuit

13. Package outline

DIP16: plastic dual in-line package; 16 leads (300 mil)

SOT38-4

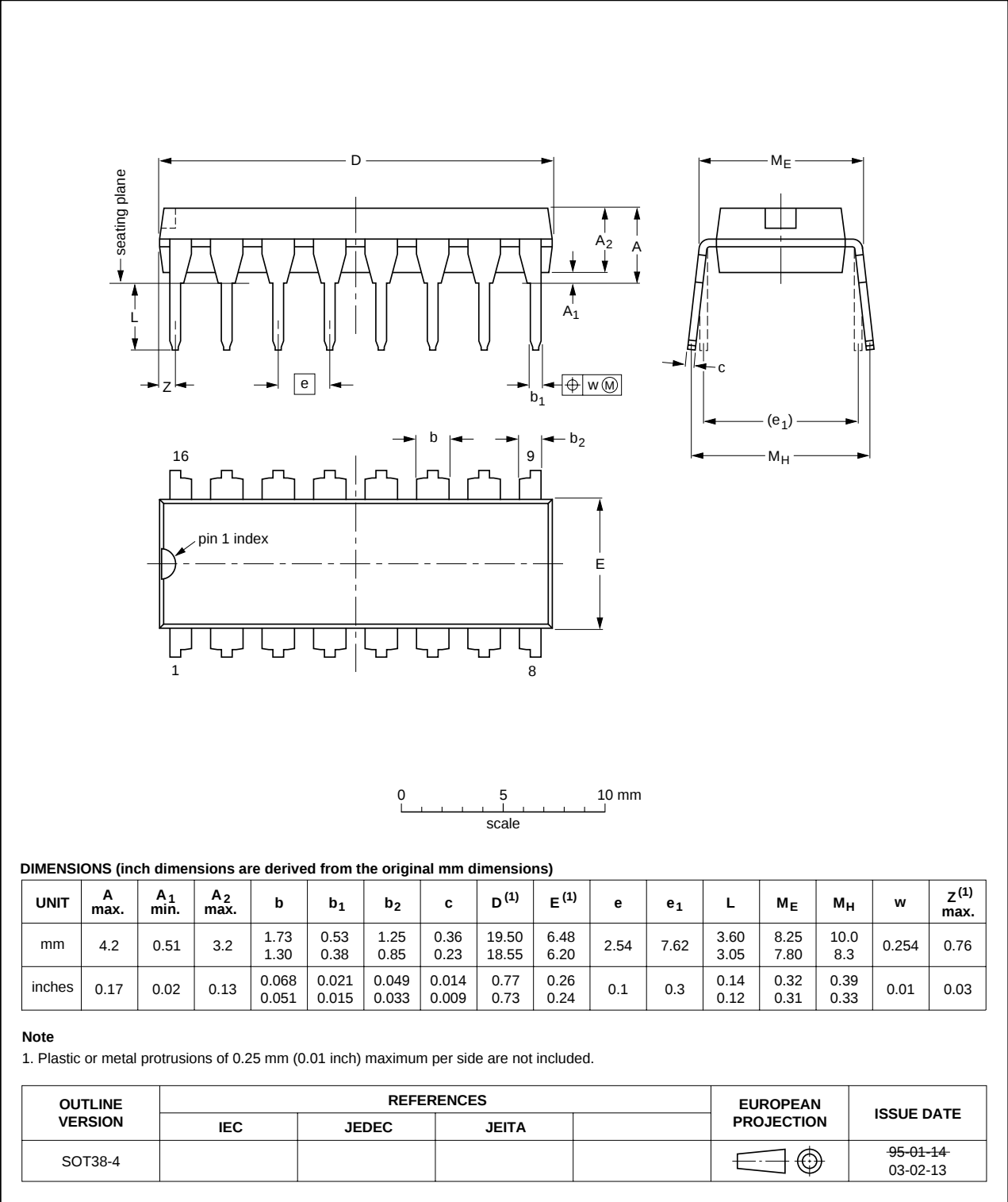
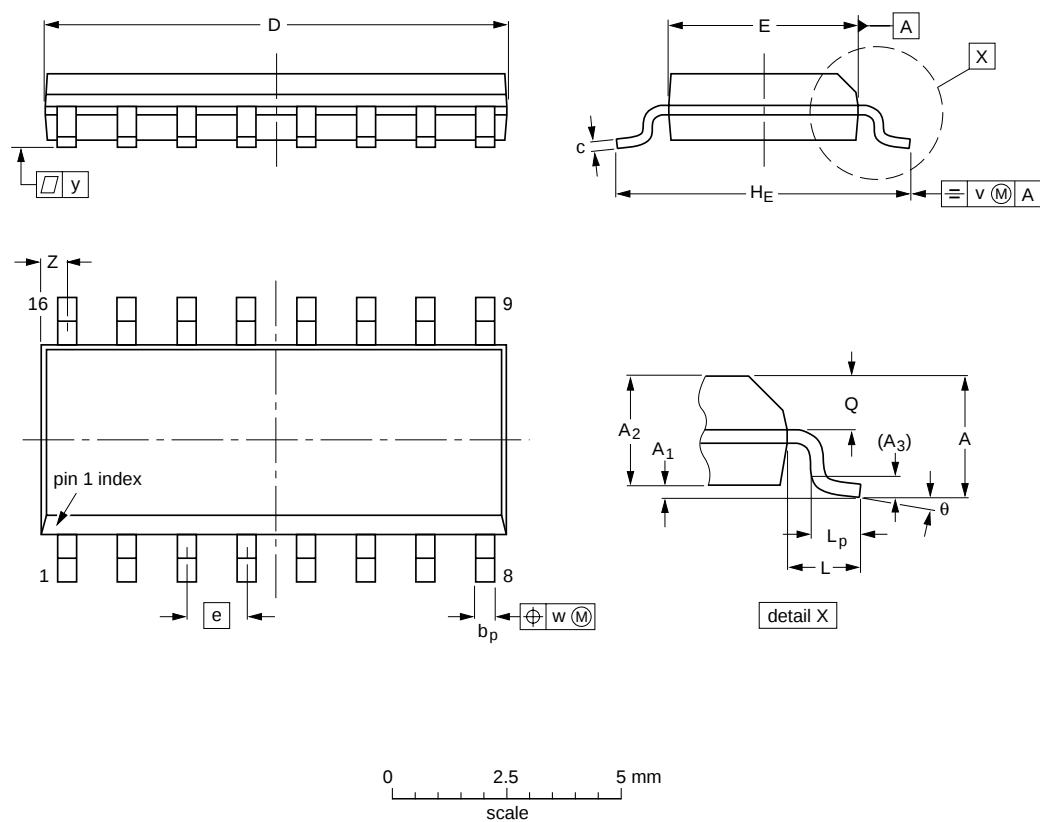


Fig 16. Package outline SOT38-4 (DIP16)

SO16: plastic small outline package; 16 leads; body width 3.9 mm

SOT109-1



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A ₁	A ₂	A ₃	b _p	c	D ⁽¹⁾	E ⁽¹⁾	e	H _E	L	L _p	Q	v	w	y	z ⁽¹⁾	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	10.0 9.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8° 0°
inches	0.069	0.010 0.004	0.057 0.049	0.01	0.019 0.014	0.0100 0.0075	0.39 0.38	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.020	0.01	0.01	0.004	0.028 0.012	

Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT109-1	076E07	MS-012				99-12-27 03-02-19

Fig 17. Package outline SOT109-1 (SO16)

DHVQFN16: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads;
16 terminals; body 2.5 x 3.5 x 0.85 mm

SOT763-1

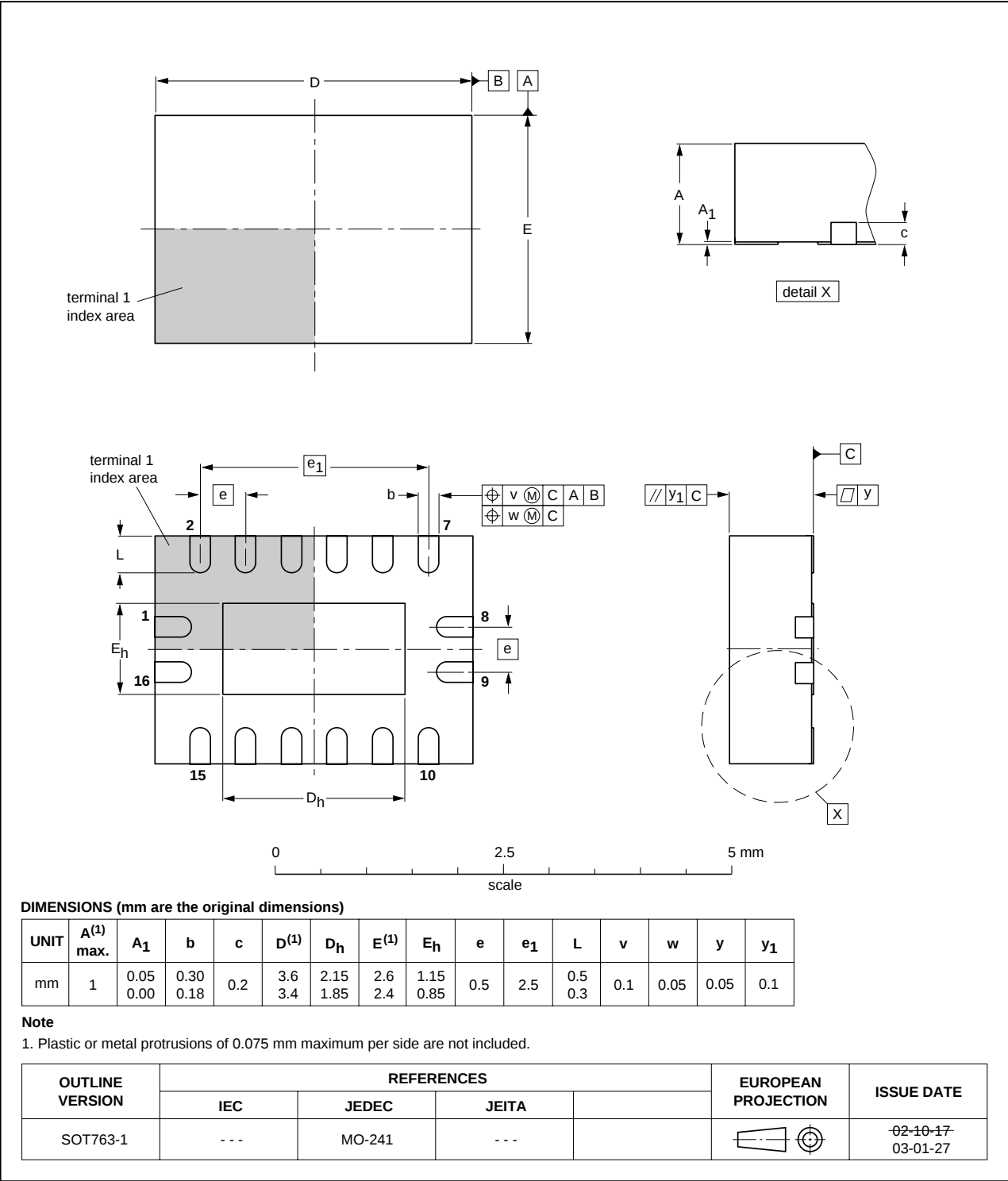


Fig 18. Package outline SOT763-1 (DHVQFN16)

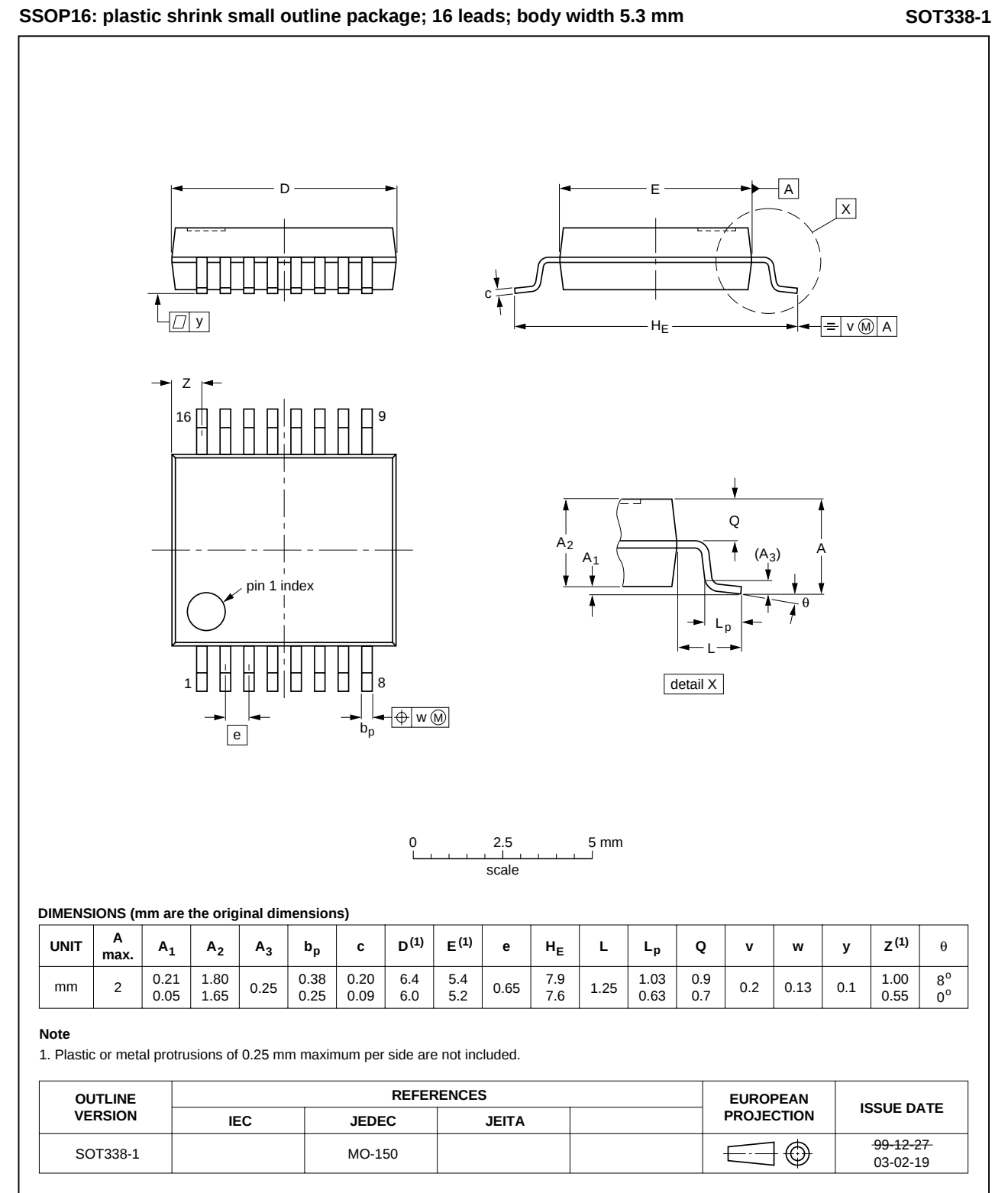


Fig 19. Package outline SOT338-1 (SSOP16)

TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm

SOT403-1

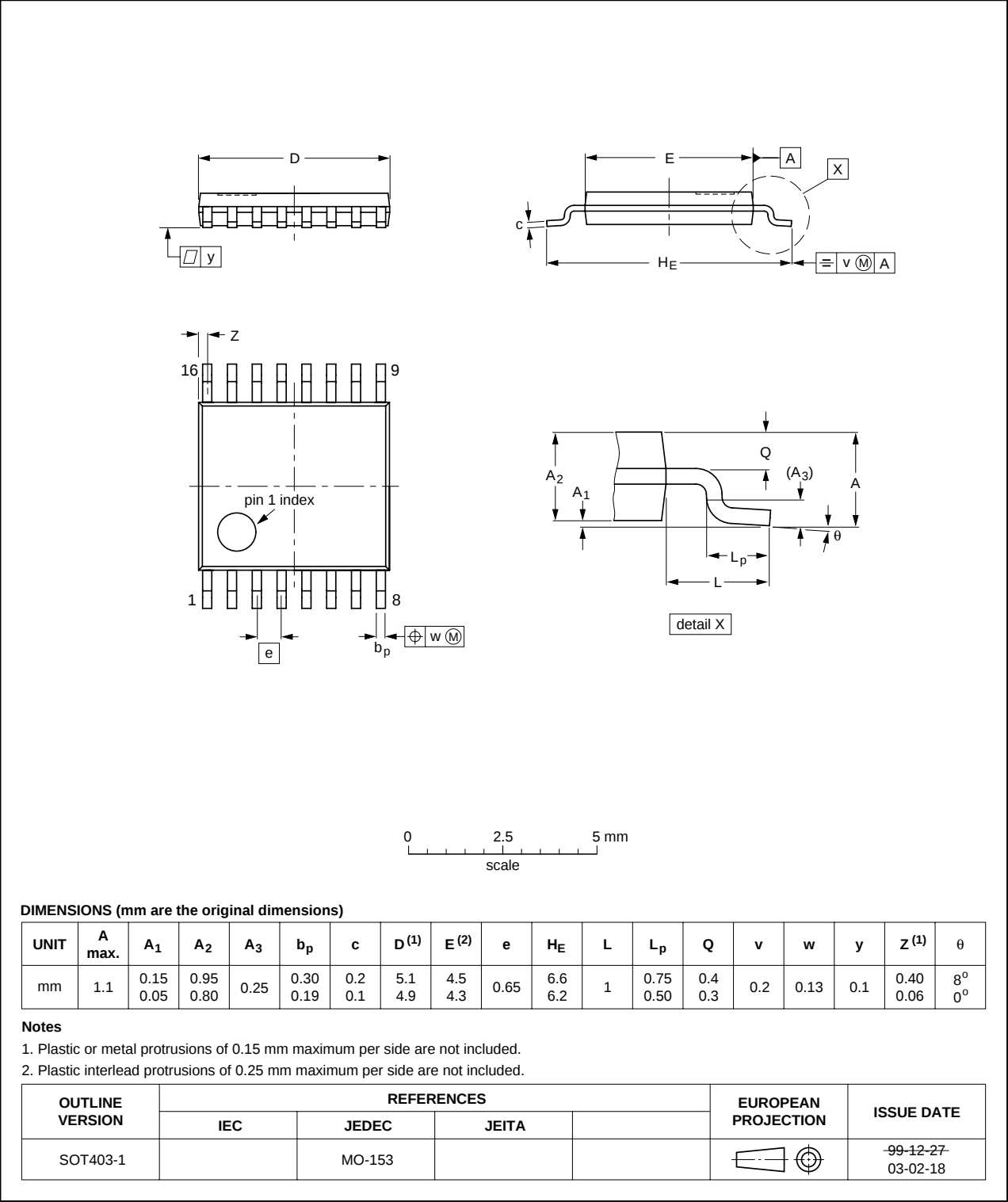


Fig 20. Package outline SOT403-1 (TSSOP16)

14. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT423_3	20080724	Product data sheet	-	74HC_HCT423_CNV_2
Modifications:	• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate. • Section 3 "Ordering information", Section 5 "Pinning information" and Section 13 "Package outline", added type numbers 74HC423BQ and 74HCT423BQ (DHVQFN16 package). • Figure 4 "Logic diagram", Figure 13 "Timing component connections" and Figure 15 "Power-down protection circuit" redrawn. • Section 10 "Dynamic characteristics" C_{PD} values added. • Figure 12 "Test circuit for measuring switching times" added. • Section 12.1 "Timing component connections" moved to Section 12. • Section 14 "Abbreviations" added.			
74HC_HCT423_CNV_2	19980708	Product specification	-	-

16. Legal information

16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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